

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-8. (Canceled)

9. (Currently Amended) A ceramic heater used in an industrial field of semiconductors, comprising:

a disk-shaped ceramic substrate; and

a heat-generation pattern disposed on a surface of said disk-shaped ceramic substrate;

wherein said disk-shaped ceramic substrate has a diameter of 200 mm or more and said disk-shaped ceramic substrate is made of at least one selected from a group essentially consisting of nitride ceramics and carbide ceramics; and

said heat-generation pattern has a bending portion arranged along an outer region of the substrate which describes an arc having a curvature radius within a range of 0.1 mm to 20 mm, so that a pattern width is constant; and

a semiconductor wafer is heated on a surface opposite to the surface of the ceramic substrate forming the heat-generating body.

10. (Previously Presented) The ceramic heater used in an industrial field of semiconductors, according to claim 9, wherein through-holes for inserting support pins are formed on the ceramic substrate.

11. (Previously Presented) The ceramic heater used in an industrial field of semiconductors, according to claim 9, wherein the bending pattern is arranged along outer regions of said disk-shaped ceramic substrate.

12. (Previously Presented) The ceramic heater used in an industrial field of semiconductors, according to claim 9, wherein a pattern width in the bending portion of the heat-generation pattern is generally constant.

13. (Previously Presented) The ceramic heater used in an industrial field of semiconductors, according to claim 9, wherein the ceramic heater is used within a temperature range from 150 to 800°C.

14. (Previously Presented) The ceramic heater used in an industrial field of semiconductors, according to claim 9, wherein the ceramic substrate has a diameter more than or equal to 300 mm.

15. (Previously Presented) The ceramic heater used in an industrial field of semiconductors, according to claim 9, wherein the ceramic substrate is made of aluminum nitride or silicon carbide.

16. (Currently Amended) A ceramic heater used in an industrial field of semiconductors, comprising:

a disk-shaped ceramic substrate; and
a heat-generation pattern disposed within said disk-shaped ceramic substrate,
wherein said disk-shaped ceramic substrate has a diameter of 200 mm or more
and said disk-shaped ceramic substrate is made of at least one selected from a group
essentially consisting of nitride ceramics and carbide ceramics; and
said heat-generation pattern has a bending portion arranged along an outer
region of the substrate which describes an arc having a curvature radius within a range of
0.1 mm to 20 mm, so that a pattern width is constant.

17 (Previously Presented) The ceramic heater used in an industrial field of semiconductors, according to claim 16, wherein through-holes for inserting support pins are formed on the ceramic substrate.

18. (Previously Presented) The ceramic heater used in an industrial field of semiconductors, according to claim 16, wherein the bending pattern is arranged along outer regions of the disk-shaped ceramic substrate.

19. (Previously Presented) The ceramic heater used in an industrial field of semiconductors, according to claim 16, wherein a pattern width in the bending portion of the heat-generation pattern is generally constant.

20. (Previously Presented) The ceramic heater used in an industrial field of semiconductors, according to claim 16, wherein the ceramic heater is used within a temperature range from 150 to 800°C.

21. (Previously Presented) The ceramic heater used in an industrial field of semiconductors, according to claim 16, wherein the ceramic substrate has a diameter more than or equal to 300 mm.

22. (Previously Presented) The ceramic heater used in an industrial field of semiconductors, according to claim 16, wherein the ceramic substrate is made of aluminum nitride or silicon carbide.